





### LOW V<sub>CE(SAT)</sub> PNP SURFACE MOUNT TRANSISTOR

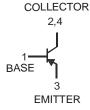
### **Features**

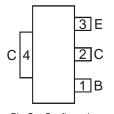
- Epitaxial Planar Die Construction
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

### **Mechanical Data**

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.115 grams (approximate)







Top View

Device Schematic

Pin Out Configuration

## **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-50	V
Emitter-Base Voltage	V <sub>EBO</sub>	-6	V
Peak Pulse Current	Ісм	-5	A
Continuous Collector Current	Ic	-3	A
Base Current	I <sub>B</sub>	-1	А

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T <sub>A</sub> = 25°C	P <sub>D</sub>	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @ T <sub>A</sub> = 25°C	$R_{ heta JA}$	125	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- 3. Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



# Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 4)						_
Collector-Base Cutoff Current	1	_	_	-100	nA	$V_{CB} = -50V, I_{E} = 0$
Collector-Base Cutoff Current	I <sub>CBO</sub>	_	_	-50	μΑ	$V_{CB} = -50V$ , $I_E = 0$ , $T_A = 150$ °C
Emitter-Base Cutoff Current	I <sub>EBO</sub>	_	_	-100	nA	$V_{EB} = -5V, I_C = 0$
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	-50	_	_	V	$I_C = -100 \mu A$
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	-50	_	_	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	-5	_	_	V	$I_E = -100 \mu A$
ON CHARACTERISTICS (Note 4)						
		200	_	_		$V_{CE} = -2V, I_{C} = -0.5A$
DC Current Gain	h <sub>FE</sub>	200	_	_	_	$V_{CE} = -2V$ , $I_C = -1A$
		100	_	_		$V_{CE} = -2V, I_{C} = -2A$
		_		-100		$I_C = -0.5A$ , $I_B = -50mA$
Collector-Emitter Saturation Voltage	V <sub>CE</sub> (SAT)	_		-180	mV	$I_C = -1A$ , $I_B = -50mA$
		_	_	-300		$I_C = -2A$ , $I_B = -200mA$
Equivalent On-Resistance	R <sub>CE(SAT)</sub>	_	67	150	mΩ	$I_E = -2A$ , $I_B = -200mA$
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	_	_	-1.2	V	$I_C = -2A$ , $I_B = -200mA$
Base-Emitter Turn-on Voltage	V <sub>BE(ON)</sub>	_	_	-1.1	V	$V_{CE} = -2V, I_{C} = -1A$
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f <sub>T</sub>	100	_	_	MHz	$V_{CE} = -5V, I_{C} = -100 \text{mA},$ f = 100MHz
Output Capacitance	C <sub>obo</sub>			40	pF	V <sub>CB</sub> = -10V, f = 1MHz

4. Measured under pulsed conditions. Pulse width =  $300\mu s$ . Duty cycle  $\leq 2\%$ . Notes:

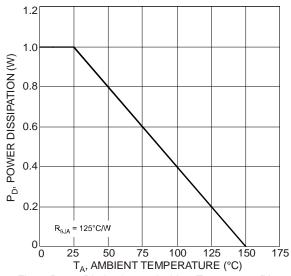
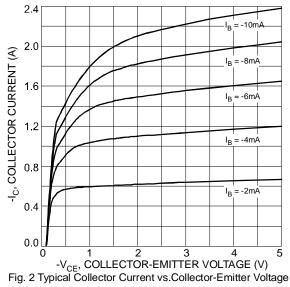
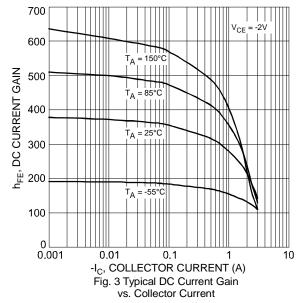
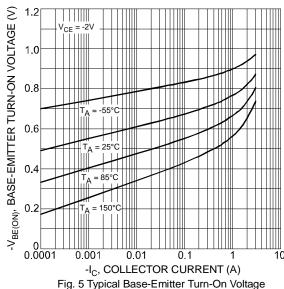


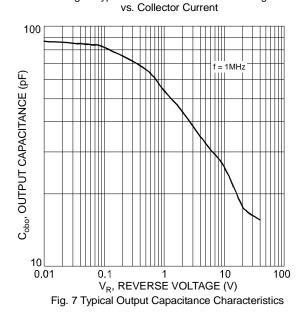
Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)











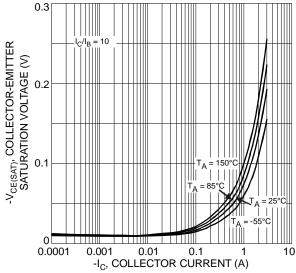


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

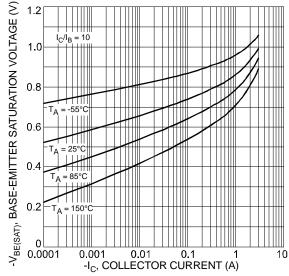


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

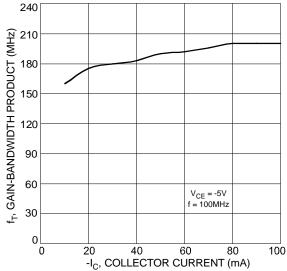


Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

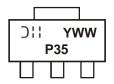


## Ordering Information (Note 5)

Part Number	Case	Packaging
DPLS350E-13	SOT-223	2500/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

# **Marking Information**



P35 = Product Type Marking Code

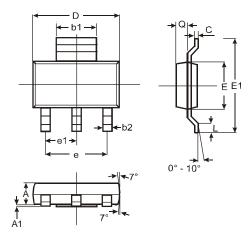
OH = Manufacturer's Code Marking

YWW = Date Code Marking

Y = Last digit of year (ex: 7 = 2007)

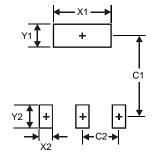
WW = Week code 01 - 52

# **Package Outline Dimensions**



SOT-223				
Dim	Min	Max	Тур	
Α	1.55	1.65	1.60	
A1	0.010	0.15	0.05	
b1	2.90	3.10	3.00	
b2	0.60	0.80	0.70	
С	0.20	0.30	0.25	
D	6.45	6.55	6.50	
Е	3.45	3.55	3.50	
E1	6.90	7.10	7.00	
е	_	_	4.60	
e1	_	_	2.30	
L	0.85	1.05	0.95	
ø	0.84	0.94	0.89	
All Dimensions in mm				

# **Suggested Pad Layout**



Dimensions	Value (in mm)
X1	3.3
X2	1.2
Y1	1.6
Y2	1.6
C1	6.4
C2	2.3



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